

In the Abstract:

Please replace the paragraph at page 23, lines 2 to 9, with a replacement paragraph amended as follows:

There is provided a method of fabricating semiconductor devices that allows ion implantation to be performed at high temperature with ions accelerated with high energy to help to introduce dopant in a semiconductor ~~substrate~~ (1, 101), substrate, in particular a SiC semiconductor substrate, at a selected region to sufficient depth. To achieve this the method includes the steps of: providing the semiconductor substrate [(1, 101)] at a surface thereof with a mask layer including a polyimide resin ~~film~~ (2), film, or a SiO₂ film (107a, 107b) and a thin metal ~~film~~ (105), film; and introducing dopant ions.

[REMARKS FOLLOW ON NEXT PAGE]